

# 2SC3403

## Silicon PNP Triple-Diffused Planar Type

High Breakdown Voltage, High Speed Switching

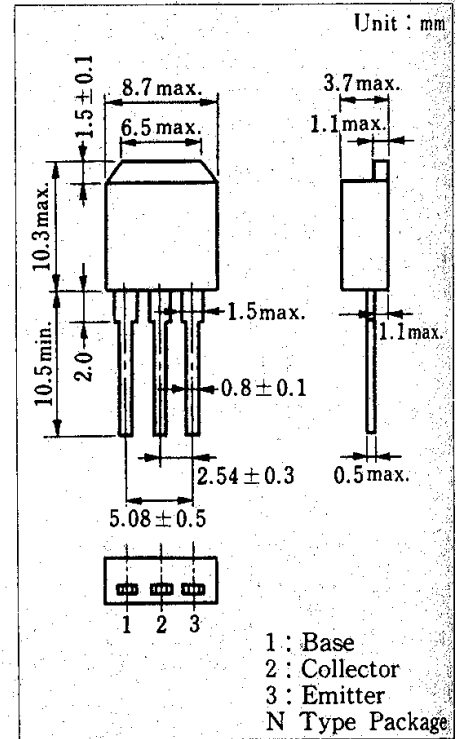
### ■ Features

- High speed switching
- Low collector-emitter saturation voltage ( $V_{CE(sat)}$ )
- "N Type" package configuration with a cooling fin for direct soldering on PC board of a small-size electronic equipment

### ■ Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ )

Item	Symbol	Value	Unit	
Collector-base voltage	$V_{CBO}$	500	V	
Collector-emitter voltage	$V_{CEO}$	400	V	
Emitter-base voltage	$V_{EBO}$	7	V	
Peak collector current	$I_{CP}$	4	A	
Collector current	$I_C$	2	A	
Collector power dissipation	$P_C$	$T_c=25^\circ\text{C}$	25	W
		$T_a=25^\circ\text{C}$	1.3	
Junction temperature	$T_j$	150	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	-55 ~ +150	$^\circ\text{C}$	

### ■ Package Dimensions



\*Surface-mount type is also available. (Refer to p.82.)

### ■ Electrical Characteristics ( $T_c=25^\circ\text{C}$ )

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB}=500\text{ V}, I_E=0$			100	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB}=5\text{ V}, I_C=0$			100	$\mu\text{A}$
Collector-emitter voltage	$V_{CEO(sus)}$	$I_C=0.2\text{ A}, L=25\text{ mH}$	400			V
DC current gain	$h_{FE1}$	$V_{CE}=5\text{ V}, I_C=0.1\text{ A}$	15			
	$h_{FE2}$	$V_{CE}=5\text{ V}, I_C=1\text{ A}$	8			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1\text{ A}, I_B=0.2\text{ A}$			1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1\text{ A}, I_B=0.2\text{ A}$			1.5	V
Transition frequency	$f_T$	$V_{CE}=10\text{ V}, I_C=0.2\text{ A}, f=1\text{ MHz}$	8			MHz
Turn-on time	$t_{on}$	$I_C=1\text{ A},$			1	$\mu\text{s}$
Storage time	$t_{stg}$	$I_{B1}=0.2\text{ A}, I_{B2}=-0.2\text{ A}$			3	$\mu\text{s}$
Fall time	$t_f$	$V_{CC}=150\text{ V}$			1	$\mu\text{s}$

\*  $V_{CEO(sus)}$  Test method

